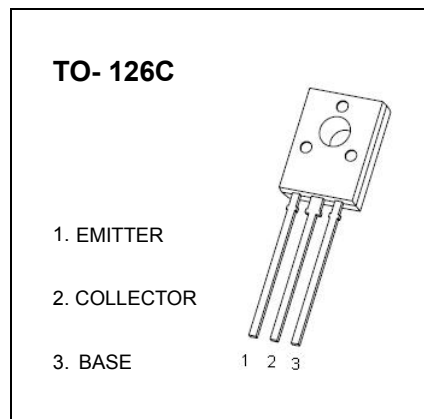


TO-126C Plastic-Encapsulate Transistors

B772 TRANSISTOR (PNP)

FEATURES

- Low speed switching



MAXIMUM RATINGS(T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _c	Collector Current -Continuous	-3	A
P _C	Collector Dissipation	1.25	W
T _J , T _{stg}	Junction and Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10 mA, I _B =0	-30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100 μA, I _C =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} = -40V, I _E =0			-1	μA
Collector cut-off current	I _{CEO}	V _{CE} =-30V, I _B =0			-10	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-6V, I _C =0			-1	μA
DC current gain	h _{FE(1)}	V _{CE} = -2V, I _C = -1A	60		400	
	h _{FE(2)}	V _{CE} =-2V, I _C = -100mA	32			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-2A, I _B = -0.2A			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-2A, I _B = -0.2A			-1.5	V
Transition frequency	f _T	V _{CE} =-5V, I _C =-0.1A f=10MHZ	50			MHz

CLASSIFICATION OF h_{FE(1)}

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

